

TECHNICAL DATA
 DATA SHEET 576, REV. B

HERMETIC POWER SCHOTTKY RECTIFIER
Very Low Forward Voltage Drop

DESCRIPTION: 45 VOLT, 30 AMP, POWER SCHOTTKY RECTIFIER IN A HERMETIC SHD-2/2B PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

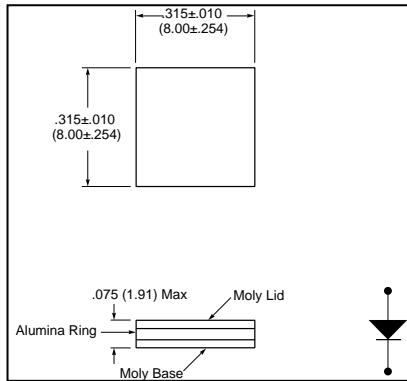
RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	45	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C = 100^\circ\text{C}$)	I_O	30	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t = 8.3\text{ms}$, Sine)	I_{FSM}	570	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_r = 5\text{V}$)	C_T	1600	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{\theta JC}$	0.90	$^\circ\text{C/W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	T_{op}/T_{stg}	-65 to +175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

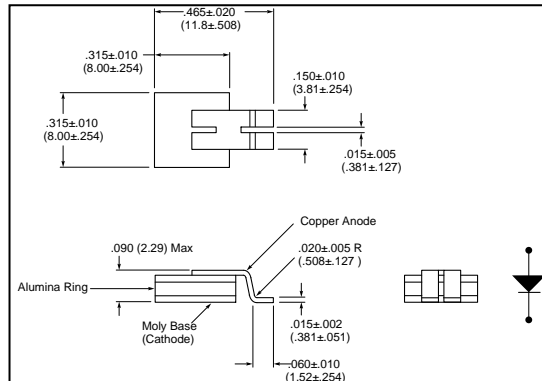
CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 30$ Amps)			
	$T_J = 25^\circ\text{C}$	V_f	0.64 Volts
	$T_J = 125^\circ\text{C}$		0.57
MAXIMUM REVERSE CURRENT (I_r @ 45 V PIV)			
	$T_J = 25^\circ\text{C}$	I_r	0.8 mA
	$T_J = 125^\circ\text{C}$		30

MECHANICAL DIMENSIONS: In Inches / mm

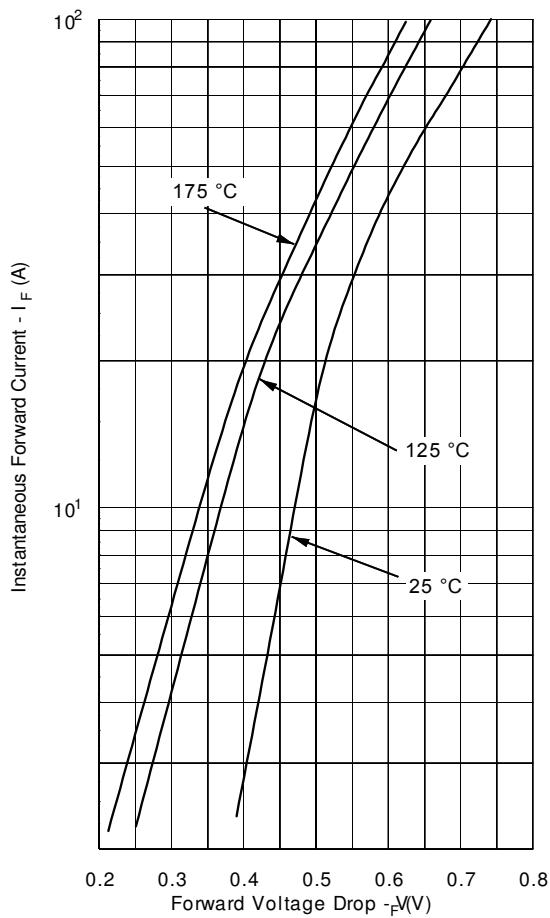
SHD-2



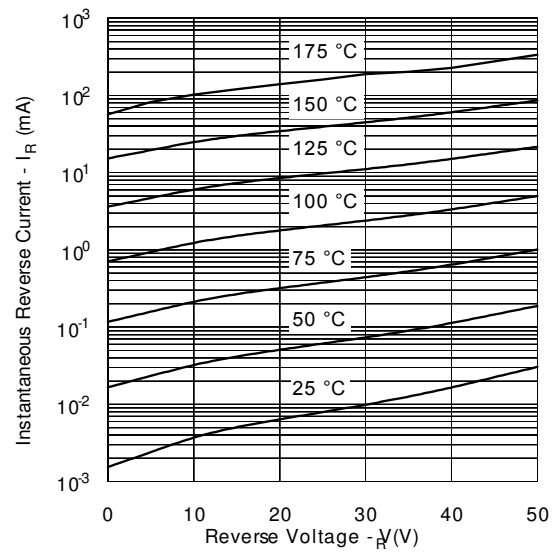
SHD-2B



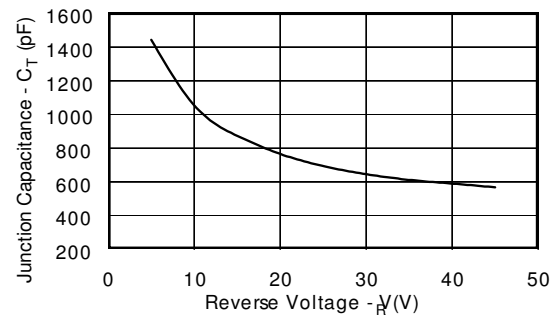
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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